

Single 2-input AND Gate

General Description

The ETQ74AHCT1G08 device is a single 2-input positive-AND gate. The device performs the Boolean function $Y = A \cdot B$ or $Y = \overline{A + B}$ in positive logic. Low I_{CC} current allows this device to be used in power-sensitive or battery-powered applications.

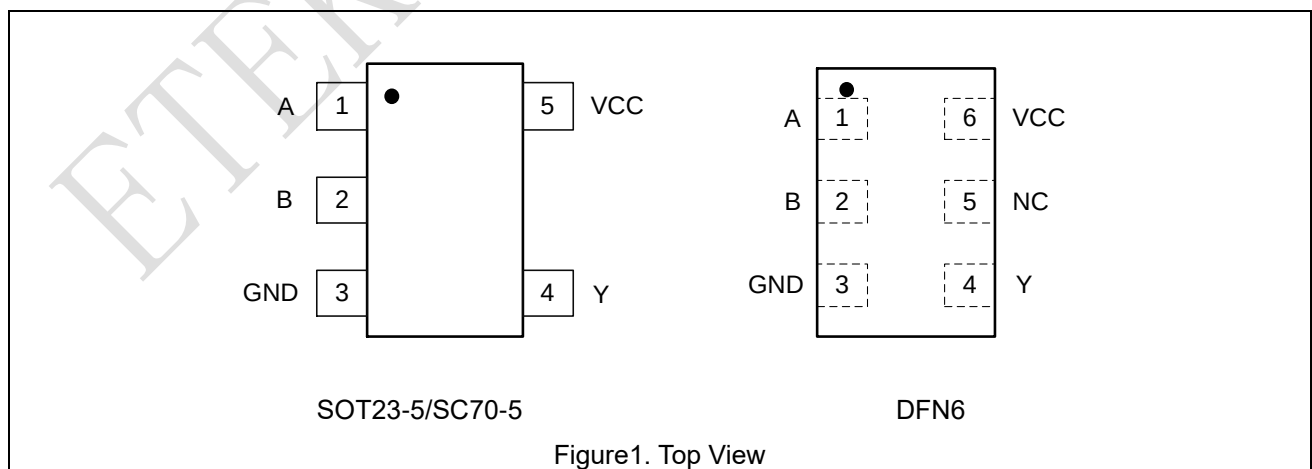
Features

- Operating Range: 4.5 V to 5.5 V
- Maximum tpd of 7.1 ns at 5 V
- Low Power Consumption: Maximum I_{CC} of 10 μ A
- ± 8 mA Output Drive at 5 V
- Inputs are TTL-Voltage Compatible
- Multiple Package Options Automotive AEC-Q100 Grade 1 Qualified
 - Ambient temperature range of -40°C to +125°C
 - ESD HBM 4KV PASS
 - ESD CDM 1KV PASS
 - Latch Up Current to 100mA PASS

Device Information

Part No.	Package	MSL
ETQ74AHCT1G08	SC70-5 (1.3mm×2.1mm)	3
ETQ74AHCT1G08T	SOT23-5 (1.6mm×2.9mm)	3
ETQ74AHCT1G08Y	DFN6 (1.0mm×1.5mm)	1

Pin Configuration



ETQ74AHCT1G08

Pin Function

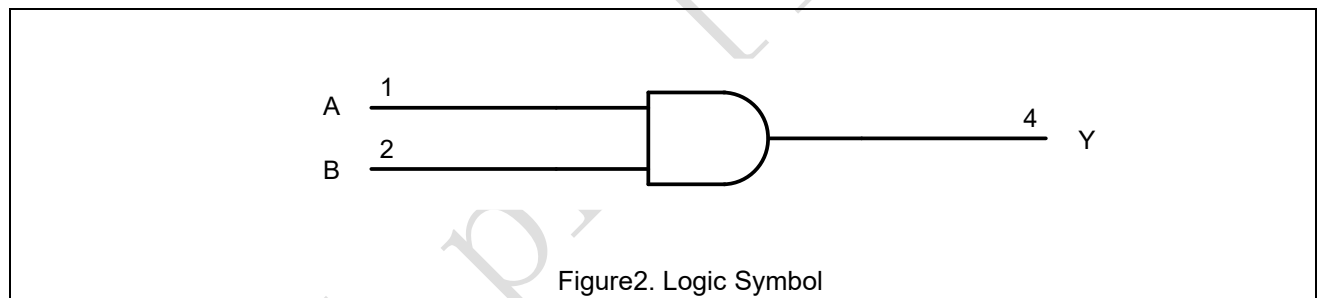
SC70-5/ SOT23-5

Pin No.	Pin Name	Function
1	A	Input A
2	B	Input B
3	GND	Ground
4	Y	Output
5	VCC	Supply Voltage

DFN6

Pin No.	Pin Name	Function
1	A	Input A
2	B	Input B
3	GND	Ground
4	Y	Output
5	NC	No connect
6	VCC	Supply Voltage

Block Diagram



Functional Description

Function Table

Input		Output
A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

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Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to 7.0	V
V _I	DC Input Voltage ⁽¹⁾		-0.5 ≤ V _I ≤ +7.0	V
V _O	DC Output Voltage Output in Higher or Low State		-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	V _I < GND	-20	mA
I _{OK}	DC Output Diode Current	V _O < GND, V _O > V _{CC}	±20	mA
I _O	DC Output Sink Current		±25	mA
I _{CC}	DC Supply Current per Supply Pin		±50	mA
I _{GND}	DC Ground Current per Supply Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T _J	Junction Temperature Under Bias		150	°C
V _{ESD}	ESD Classification	Human Body Model ⁽²⁾	±4000	V
		Charged Device Model ⁽³⁾	±1000	
I _{LU}	Latch-up Current Above V _{CC} and GND at 125°C ⁽⁴⁾		±100	mA

Stresses exceeding those listed in this table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note1: I_O absolute maximum rating must be observed;

Note2: HBM tested per AEC-Q100-002(EIA/JESD22-A114);

Note3: CDM tested per AEC-Q100-011(EIA/JESD22-C101);

Note4: Latch up Current Maximum Rating tested per AEC-Q100-004(EIA/JESD78E);

Thermal Characteristics

Symbol	Package	Ratings	Value	Unit
R _{θJA}	SC70-5	Thermal Characteristics, Thermal Resistance, Junction-to-Air	300	°C/W
	SOT23-5		250	
	DFN6(1.0×1.5)		440	
R _{θJB}	SC70-5	Thermal Characteristics, Thermal Resistance, Junction-to-board	75	°C/W
	SOT23-5		65	
	DFN6(1.0×1.5)		270	

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Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	4.5	5.5	V
V _{IH}	High-level Input Voltage	2		V
V _{IL}	Low-level Input Voltage		0.8	V
V _I	Input Voltage	0	5.5	V
V _O	Output Voltage	0	V _{CC}	V
I _{OH}	High-level Output Current		-8	mA
I _{OL}	Low-level Output Current		8	mA
Δt/Δv	Input Transition Rise and Fall Rate		20	ns/V
T _A	Operating Temperature Range	-40	125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied.

Electrical Characteristics

DC Electrical Characteristics

Symbol	Parameter	Condition	V _{CC} (V)	T _A =25°C			-40°C≤T _A ≤125°C		Unit
				Min	Typ	Max	Min	Max	
V _{OH}	High-Level Output Voltage	I _{OH} =-50μA	4.5	4.4	4.5		4.4		V
		I _{OH} =-8mA	4.5	3.94			3.8		
V _{OL}	Low-Level Output Voltage	I _{OL} =50μA	4.5			0.1		0.1	V
		I _{OL} =8mA	4.5			0.36		0.44	
I _I	Input Current	V _{IN} = 5.5V or GND	0 to 5.5			±0.1		±1	μA
I _{CC}	Supply Current	V _{IN} = V _{CC} or GND, I _O = 0	5.5			1.0		10	μA
ΔI _{CC} ⁽⁵⁾	Change in Supply Current	One input at 3.4 V, Other Inputs at V _{CC} or GND	5.5			1.35		1.5	mA
C _I	Input Capacitance	V _{IN} = V _{CC} or GND	5		4	10			pF

Note5: This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.

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Switching Characteristics

Over recommended operating free-air temperature range, $V_{CC} = 5V \pm 0.5V$ (unless otherwise noted)
(see Figure 3)

Symbol	Parameter	Condition	$T_A = 25^\circ\text{C}$			$-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$		$-40^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}	Propagation Delay	$C_L = 15\text{pF}$		5	6.2	1	7.1	1	7.5	ns
t_{PHL}		$C_L = 15\text{pF}$		5	6.2	1	7.1	1	7.5	ns
t_{PLH}		$C_L = 50\text{pF}$		5.5	7.9	1	9	1	10	ns
t_{PHL}		$C_L = 50\text{pF}$		5.5	7.9	1	9	1	10	ns

Operating Characteristics

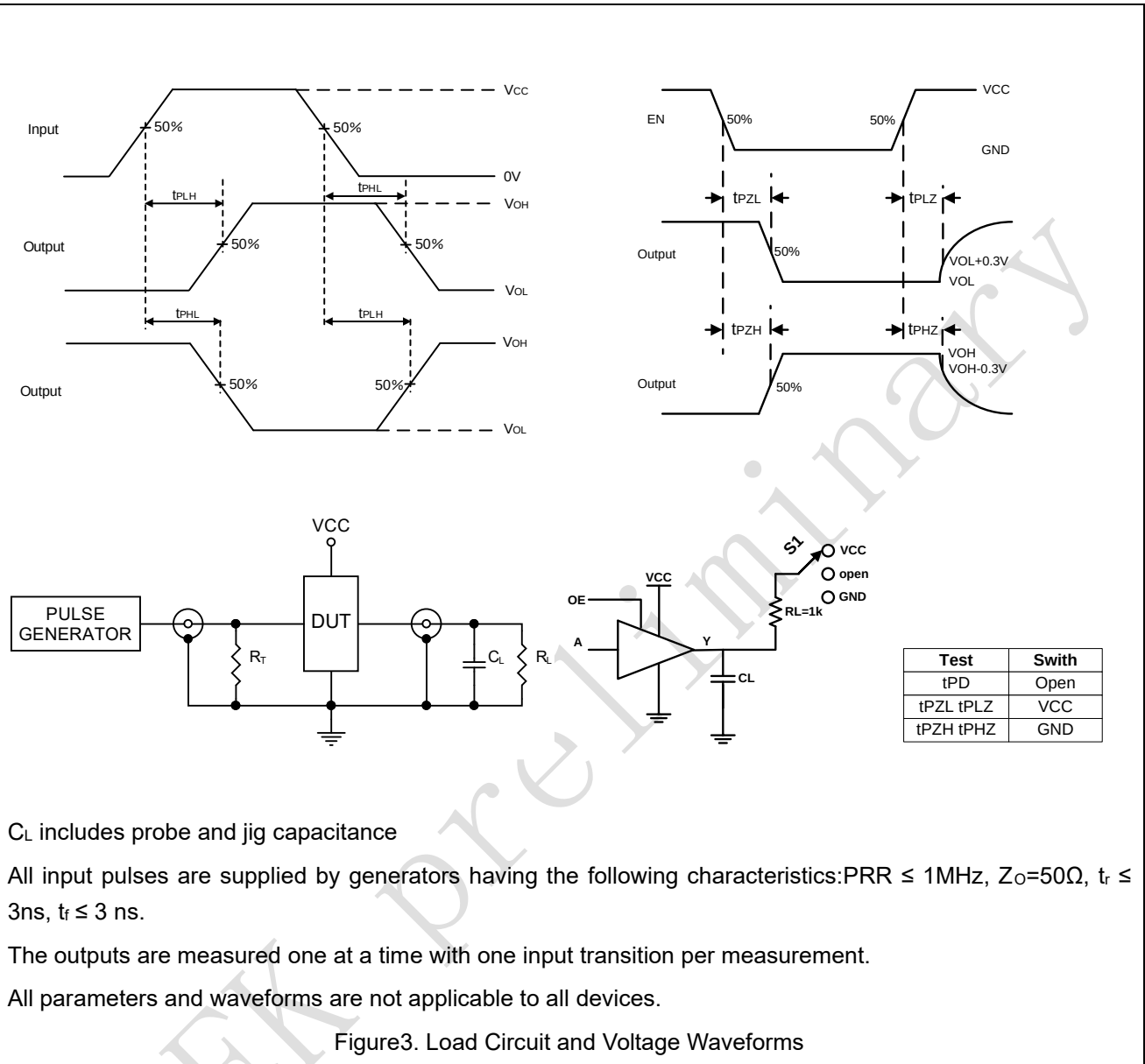
$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

Symbol	Parameter	Condition	Typ	Unit
C_{PD}	Power Dissipation Capacitance ⁽⁶⁾	No load, $f = 1\text{ MHz}$	18	pF

Note6: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \times V_{CC} \times f_{in} + I_{CC} \times C_{PD}$ is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \times V_{CC}^2 \times f_{in} + I_{CC} \times V_{CC} \times Fig.$

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Waveform and Test Circuit



C_L includes probe and jig capacitance

All input pulses are supplied by generators having the following characteristics: PRR ≤ 1MHz, Z_O=50Ω, t_r ≤ 3ns, t_f ≤ 3 ns.

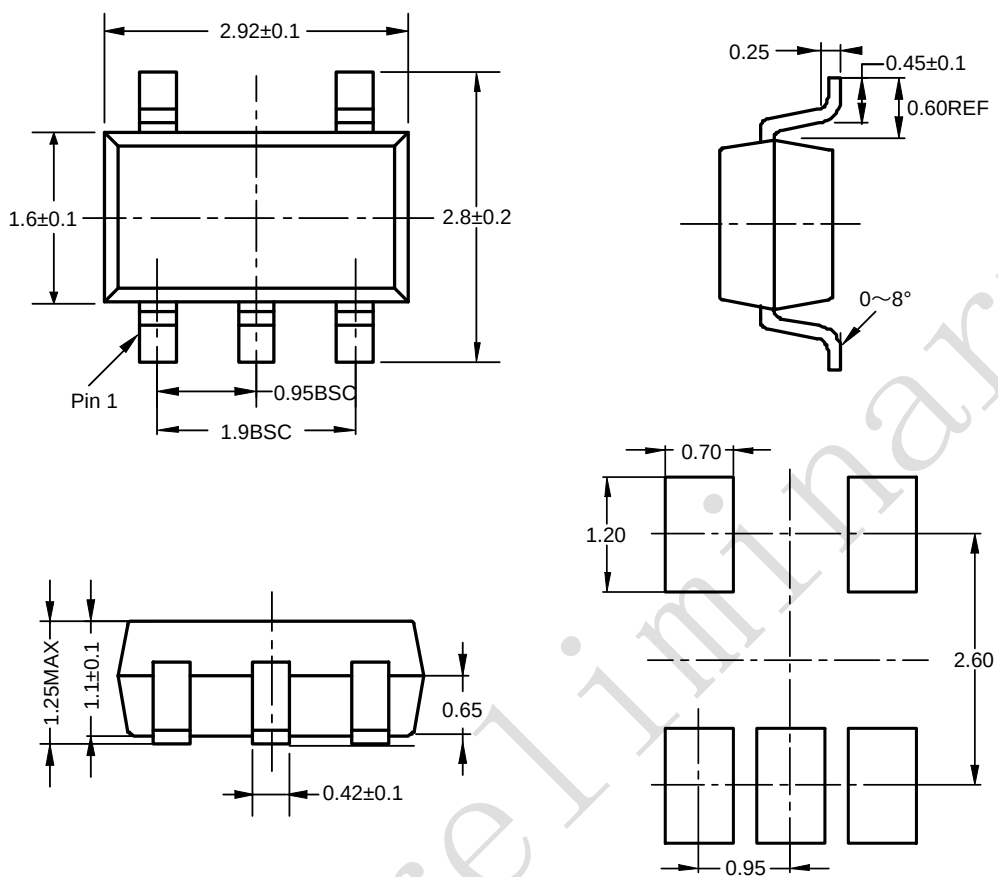
The outputs are measured one at a time with one input transition per measurement.

All parameters and waveforms are not applicable to all devices.

Figure3. Load Circuit and Voltage Waveforms

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SOT23-5

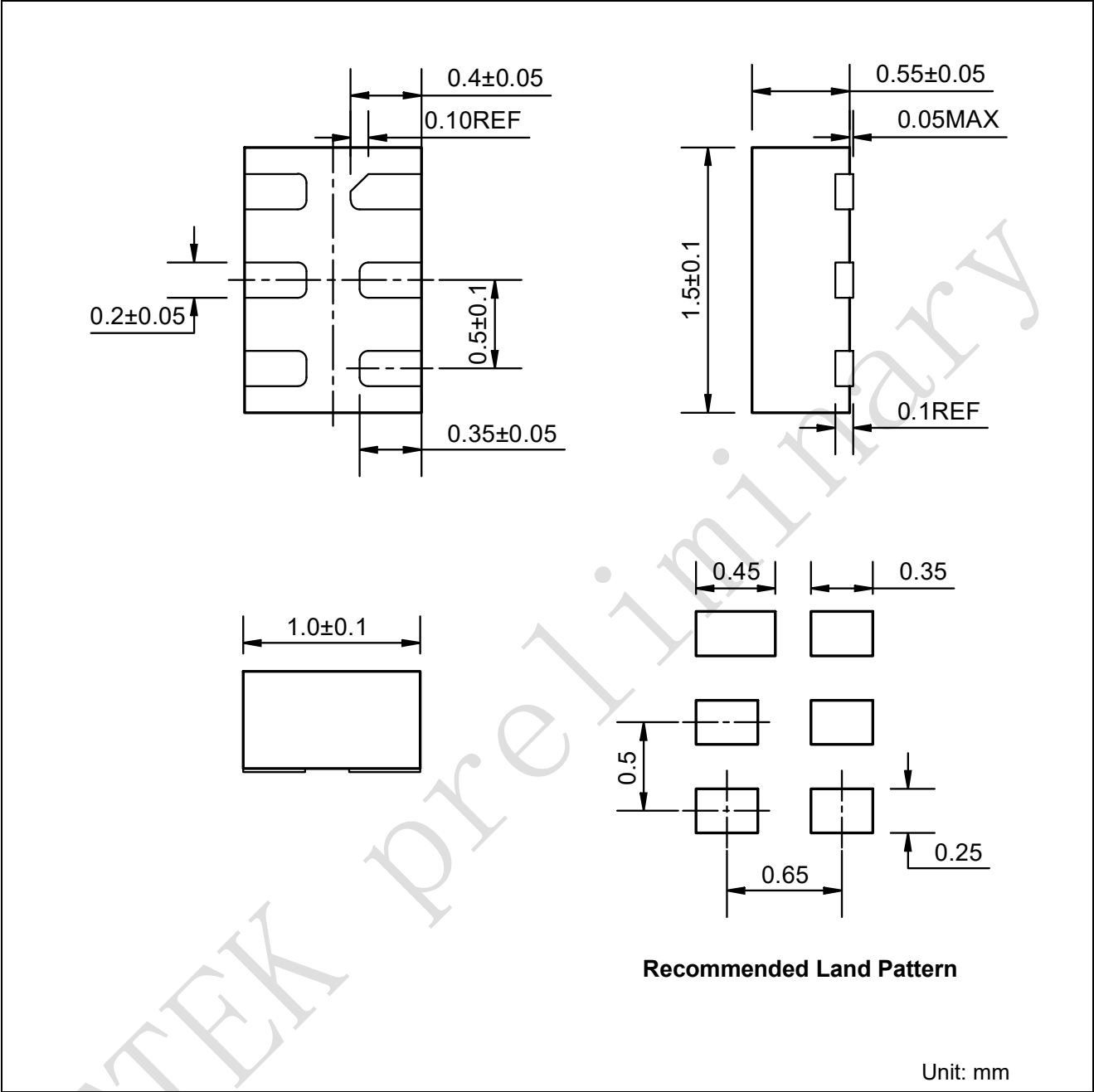


Recommended Land Pattern

Unit: mm

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DFN6 (1.0×1.5)



Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
0.0	2025-05-08	Preliminary Version	Yuyifan	Yangxiaoxu	Liujiy